

I claim:

1. A method of CMP comprising:
forming a CMP slurry containing cerium oxide;
adding a slurry modifier to the slurry, wherein the slurry
5 modifier polishes low structure areas at a substantially zero rate and
polishes high structure areas at a rate approximating a blanket polishing
rate; and
polishing a structure using the modifier-contained slurry.
2. The method of claim 1 wherein said forming includes setting
a cerium oxide concentration of between about 1% and 50% by weight.
3. The method of claim 1 wherein said polishing includes CMP
at a pressure of between about five psi and ten psi.
4. The method of claim 1 wherein said adding includes adding
ethylene glycol at a concentration of up to 50%.
5. A method of CMP comprising:
forming a CMP slurry containing cerium oxide at a
concentration of between about 1% and 50% by weight;
adding a slurry modifier to the slurry, wherein the slurry
5 modifier polishes low structure areas at a substantially zero rate and
polishes high structure areas at a rate approximating a blanket polishing
rate; and
polishing a structure using the modifier-contained slurry.

6. The method of claim 5 wherein said polishing includes CMP at a pressure of between about five psi and ten psi.

7. The method of claim 5 wherein said adding includes adding ethylene glycol at a concentration of up to 50%.

8. A method of CMP comprising:

forming a CMP slurry containing cerium oxide at a concentration of between about 1% and 50% by weight;

5 adding ethylene glycol at a concentration of up to 50% for polishing low structure areas at a substantially zero rate and polishing high structure areas at a rate approximating a blanket polishing rate; and polishing a structure using the slurry.

9. The method of claim 8 wherein said polishing includes CMP at a pressure of between about five psi and ten psi.